

N-Channel Enhancement-Mode Vertical DMOS FET

Features

- ► Low threshold (1.6V max.)
- High input impedance
- ► Low input capacitance (110pF typical)
- Fast switching speeds
- ▶ Low on-resistance
- Free from secondary breakdown
- Low input and output leakage
- ► Complementary N- and P-channel devices

Applications

- Logic level interfaces ideal for TTL and CMOS
- Solid state relays
- Battery operated systems
- Photo voltaic drives
- Analog switches
- General purpose line drivers
- ► Telecom switches

General Description

This low threshold, enhancement-mode (normally-off) transistor utilizes a vertical DMOS structure and Supertex's well-proven, silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Ordering Information

| Device | Package Option | BV _{DSS} /BV _{DGS} | R _{DS(ON)} | D _(ON) | V _{GS(th)} (max) (V) | |
|--------|----------------|--------------------------------------|---------------------|-------------------|-------------------------------------|--|
| Device | TO-92 | (V) | (max) (Ω) | (min) (A) | | |
| TN0620 | TN0620N3-G | 200 | 6.0 | 1.0 | 1.6 | |

⁻G indicates package is RoHS compliant ('Green')





Absolute Maximum Ratings

| Parameter | Value |
|-----------------------------------|-------------------|
| Drain-to-source voltage | BV _{DSS} |
| Drain-to-gate voltage | BV_{DGS} |
| Gate-to-source voltage | ±20V |
| Operating and storage temperature | -55°C to +150°C |
| Soldering temperature* | 300°C |

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

Pin Configurations



Product Marking



YY = Year Sealed WW = Week Sealed _____ = "Green" Packaging

TO-92 (N3)

Distance of 1.6mm from case for 10 seconds.

Thermal Characteristics

| Package | I _D (continuous) [†] (mA) | I _D (pulsed) (A) | Power Dissipation @T _c = 25°C (W) | θ _{jc} (°C/W) | θ _{ja} (°C/W) | l _{DR} † (mA) | I _{DRM} (A) |
|---------|---|-----------------------------------|--|---------------------------|---------------------------|---------------------------|----------------------|
| TO-92 | 250 | 2.0 | 1.0 | 125 | 170 | 250 | 2.0 |

Notes:

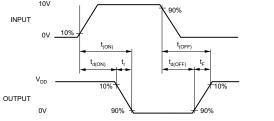
Electrical Characteristics (T_A = 25°C unless otherwise specified)

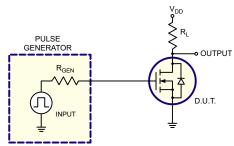
| Sym | Parameter | Min | Тур | Max | Units | Conditions | |
|---------------------|--|-----|-----|------|-------|--|--|
| BV _{DSS} | Drain-to-source breakdown voltage | 200 | - | - | V | $V_{GS} = 0V, I_{D} = 2.0 \text{mA}$ | |
| $V_{\rm GS(th)}$ | Gate threshold voltage | 0.6 | 1 | 1.6 | V | $V_{GS} = V_{DS}$, $I_{D} = 1.0$ mA | |
| $\Delta V_{GS(th)}$ | Change in V _{GS(th)} with temperature | - | - | -5.0 | mV/°C | $V_{GS} = V_{DS}$, $I_{D} = 1.0$ mA | |
| I _{GSS} | Gate body leakage | - | - | 100 | nA | $V_{GS} = \pm 20V, V_{DS} = 0V$ | |
| | | - | - | 10 | μA | $V_{GS} = 0V, V_{DS} = Max Rating$ | |
| l _{DSS} | Zero gate voltage drain current | - | - | 1.0 | mA | $V_{DS} = 0.8$ Max Rating, $V_{GS} = 0V$, $T_{A} = 125$ °C | |
| | On-state drain current | 0.5 | - | - | A | $V_{GS} = 5.0V, V_{DS} = 25V$ | |
| D(ON) | On-state drain current | 1.0 | - | - | ^ | $V_{GS} = 10V, V_{DS} = 25V$ | |
| D | Static drain-to-source on-state resistance | - | 6.0 | 8.0 | Ω | $V_{GS} = 5.0V, I_{D} = 250mA$ | |
| R _{DS(ON)} | Static drain-to-source on-state resistance | | 4.0 | 6.0 | \$2 | $V_{GS} = 10V, I_{D} = 500mA$ | |
| $\Delta R_{DS(ON)}$ | Change in R _{DS(ON)} with temperature | - | - | 1.4 | %/°C | $V_{GS} = 10V, I_{D} = 500mA$ | |
| G _{FS} | Forward transductance | 300 | 400 | - | mmho | $V_{DS} = 25V, I_{D} = 500mA$ | |
| C _{ISS} | Input capacitance | - | 110 | 150 | | V _{GS} = 0V, | |
| C _{oss} | Common source output capacitance | - | 40 | 85 | pF | $V_{DS} = 25V,$ | |
| C _{RSS} | Reverse transfer capacitance | - | 10 | 35 | | f = 1.0MHz | |
| t _{d(ON)} | Turn-on delay time | - | - | 10 | | \\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ | |
| t _r | Rise time Turn-off delay time | | - | 8.0 | ns | $V_{DD} = 25V,$ $I_{D} = 1.0A,$ $R_{GEN} = 25\Omega$ | |
| t _{d(OFF)} | | | - | 20 | | | |
| t _f | Fall time | - | - | 20 | | GEN | |
| V _{SD} | Diode forward voltage drop | - | - | 1.8 | V | $V_{GS} = 0V, I_{SD} = 1.0A$ | |
| t _{rr} | Reverse recovery time | - | 300 | - | ns | $V_{GS} = 0V, I_{SD} = 1.0A$ | |

Notes:

- 1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)
- 2. All A.C. parameters sample tested.

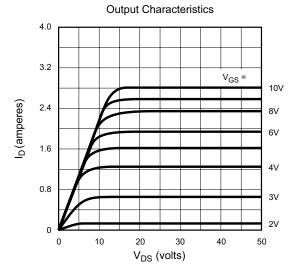
Switching Waveforms and Test Circuit

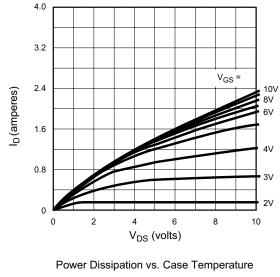




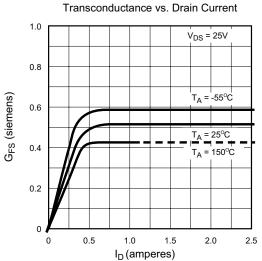
[†] I_D (continuous) is limited by max rated T_i .

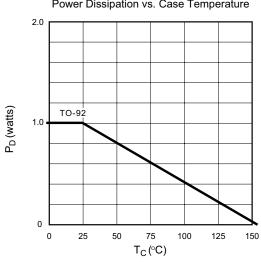
Typical Performance Curves

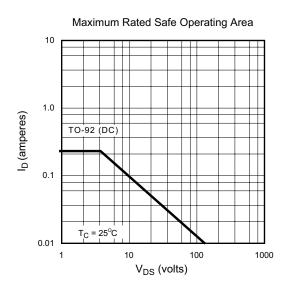


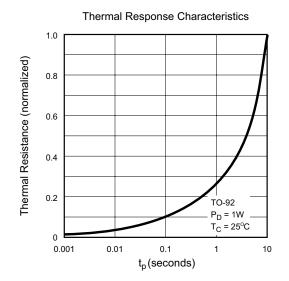


Saturation Characteristics

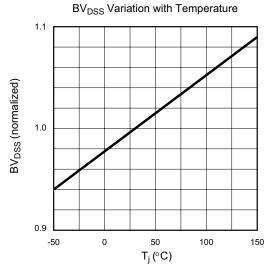


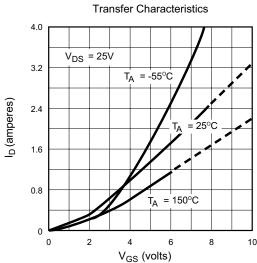


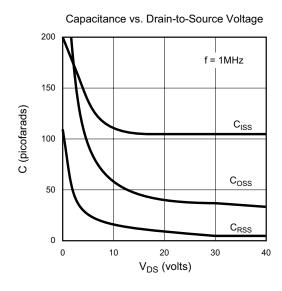


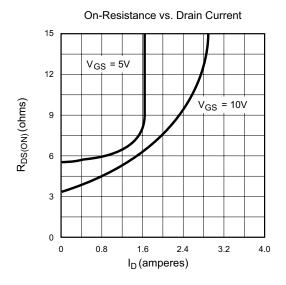


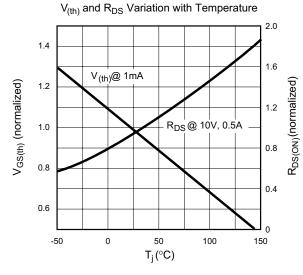
Typical Performance Curves (cont.)

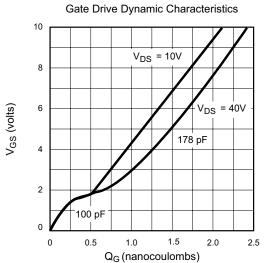




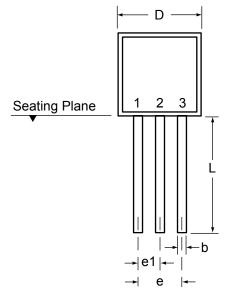


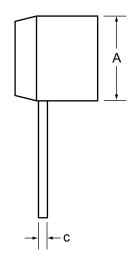






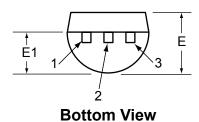
3-Lead TO-92 Package Outline (N3)





Front View

Side View



| Symbol | | Α | b | С | D | E | E1 | е | e1 | L |
|---------------------|-----|------|-------------------|-------------------|------|------|------|------|------|-------|
| Dimensions (inches) | MIN | .170 | .014 [†] | .014 [†] | .175 | .125 | .080 | .095 | .045 | .500 |
| | NOM | - | - | - | - | - | - | - | - | - |
| | MAX | .210 | .022 [†] | .022 [†] | .205 | .165 | .105 | .105 | .055 | .610* |

JEDEC Registration TO-92.

Drawings not to scale.

Supertex Doc.#: DSPD-3TO92N3, Version D080408.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to http://www.supertex.com/packaging.html.)

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^{*} This dimension is not specified in the original JEDEC drawing. The value listed is for reference only.

[†] This dimension is a non-JEDEC dimension.